

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	10/074884	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:30
L2	10359	((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:31
L3	1945	((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:32
L4	1004	semiconductor same ((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:32
L5	668	semiconductor same ((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness) same nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:32
L6	647	semiconductor same ((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness) same nitride same oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:32
L7	605	semiconductor same ((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness) same nitride same oxide same silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:32
L8	17	(semiconductor same ((oxide near10 nitride) or oxynitride) near10 (gate adj (insulating or dielectric)) with (thick or thickness) same nitride same oxide same silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:33
L9	2837	(oxide same nitride same (stack or stacking or stacked) same (gate adj (dielectric or insulating)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:37

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L10	1111	(oxide with nitride with (stack or stacking or stacked) with (gate adj (dielectric or insulating)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:37
L11	119	(oxide with nitride with (stack or stacking or stacked) with (gate adj (dielectric or insulating))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:38
L12	0	(oxide with nitride with (stack or stacking or stacked) with (gate adj (dielectric or insulating))).clm. and 257/635.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:38
L13	0	(oxide with nitride with (stack or stacking or stacked) with (gate adj (dielectric or insulating))) and 257/635.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:39
L14	7	(oxide with nitride with (gate adj (dielectric or insulating))) and 257/635.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:40
L15	8044	(gate adj (dielectric or insulating)). clm. and (gate adj (dielectric or insulating)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:40
L16	544	(gate adj (dielectric or insulating)). clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:40
L17	106791	(gate adj (dielectric or insulating)). clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:41
L18	91721	(gate adj (dielectric or insulating)). clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:41
L19	331	(gate adj (dielectric or insulating)). clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:42

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L20	184	(gate adj (dielectric or insulating)).clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab. and ((silicon near nitride) or sin).clm. and ((silicon near oxide) or sio)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:42
L21	154	(gate adj (dielectric or insulating)).clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab. and ((silicon near nitride) or sin).clm. and ((silicon near oxide) or sio).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:42
L22	126	(gate adj (dielectric or insulating)).clm. and (gate adj (dielectric or insulating)).ab. and nitride.clm. and nitride.ab. and oxide.clm. and oxide.ab. and ((silicon near nitride) or sin).clm. near10 ((silicon near oxide) or sio).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:55
L23	57	(ramkumar near10 krishnaswamy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:01
L24	5	(ramkumar near10 krishnaswamy) and (gate near (dielectric or insulating)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:58
L25	0	(ramkumar near10 krishnaswamy) and ((gate near (dielectric or insulating)) with nitride with oxide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:58
L26	1	(ramkumar near10 krishnaswamy) and ((gate near (dielectric or insulating)) same nitride same oxide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 15:59
L27	11649	(gate near10 (dielectric or insulating)) near10 oxide near10 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:01

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L28	8136	(gate near2 (dielectric or insulating) near10 oxide near10 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:01
L29	752	(gate near2 (dielectric or insulating) near10 oxide near10 nitride near10 (stack or stacking or stacked))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:01
L30	95	(gate near2 (dielectric or insulating) near10 oxide near10 nitride near10 (stack or stacking or stacked)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:03
L31	31	(gate near2 (dielectric or insulating) near10 oxide near2 nitride near2 (stack or stacking or stacked)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:04
L32	5	(gate near2 (dielectric or insulating) near10 oxide near2 nitride near2 (stack or stacking or stacked)).clm. and (gate adj (dielectric or insulating)).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:05
L33	54	(gate near2 (dielectric or insulating) near10 oxide near10 nitride).clm. and (gate adj (dielectric or insulating)).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:07
L34	17049	257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or "E21.""66".ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:10
L35	18025	257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:10

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L36	3619	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:10
L37	1144	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. and ((silicon near2 (oxide or dioxide)) or SiO).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:11
L38	924	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. and ((silicon near2 (oxide or dioxide)) or SiO).clm. and ((silicon near2 (nitride)) or SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:11
L39	619	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. and ((silicon near2 (oxide or dioxide)) or SiO).clm. and ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:11

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L40	263	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)). clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. and ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:12
L41	143	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)). clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:12
L42	0	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)). clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with ((silicon near2 (nitride)) or SiN).clm. and 257/635.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:13

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L43	143	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:14
L44	24	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with (stack or stacking or stacked).clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:15
L45	0	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with (stack or stacking or stacked).clm. with (thick or thickness).clm. with angstrom.clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:16

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L46	0	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. with ((silicon near2 (oxide or dioxide)) or SiO).clm. with (thick or thickness).clm. with angstrom. clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:16
L47	6	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. same ((silicon near2 (oxide or dioxide)) or SiO).clm. same (thick or thickness).clm. with angstrom. clm. with ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:16
L48	6	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)).clm. same ((silicon near2 (oxide or dioxide)) or SiO).clm. same (thick or thickness).clm. with angstrom. clm. same ((silicon near2 (nitride)) or SiN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:17

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L49	6	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)) same ((silicon near2 (oxide or dioxide)) or SiO) same (thick or thickness).clm. same angstrom same ((silicon near2 (nitride)) or SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:18
L50	143	(257/635.ccls. or 257/410.ccls. or 257/411.ccls. or 257/412.ccls. or 257/286.ccls. or 257/287.ccls. or 257/312.ccls. or 257/313.ccls. or 257/316.ccls. or 438/287.ccls. or 438/197.ccls. or 438/216.ccls. or 438/238.ccls. or 257/296.ccls. or 257/E21.625.ccls. or 257/E21.654.ccls. or 257/E21.66.ccls.) and (gate adj (dielectric or insulating)) same ((silicon near2 (oxide or dioxide)) or SiO) same (thick or thickness) same angstrom same ((silicon near2 (nitride)) or SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/02 16:18